

isc N-Channel MOSFET Transistor

4N55

DESCRIPTION

- Drain Current $I_D = 4A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 550V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

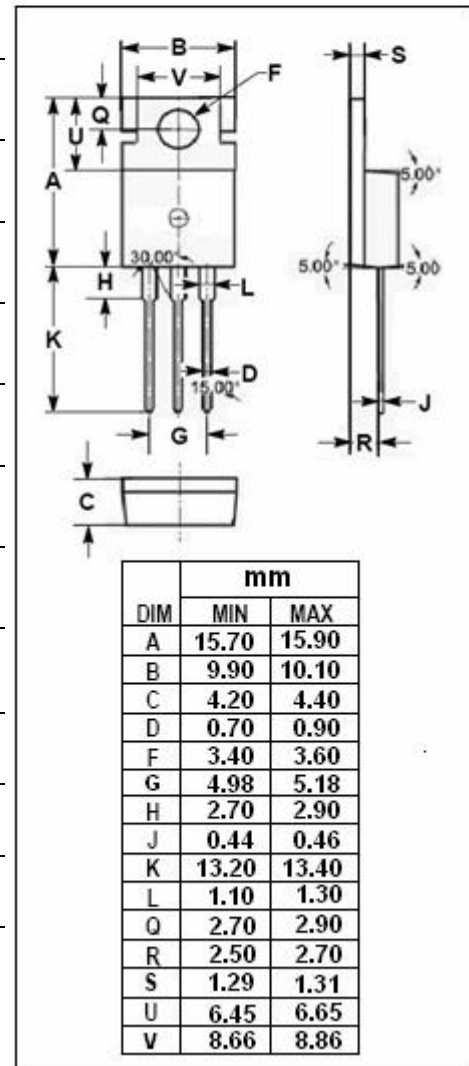
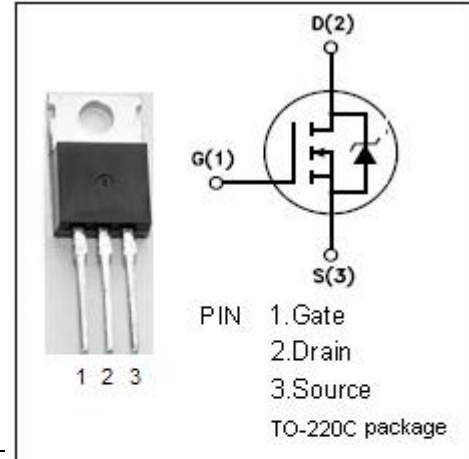
- General purpose power amplifier

ABSOLUTE MAXIMUM RATINGS($T_C = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	550	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C = 25^\circ C$	4	A
$I_{D(\text{puls})}$	Pulse Drain Current	10	A
P_{tot}	Total Dissipation@ $T_C = 25^\circ C$	40	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{\text{th j-c}}$	Thermal Resistance, Junction to Case	3	$^\circ C/W$
$R_{\text{th j-a}}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$



isc N-Channel MOSFET Transistor**4N55**• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=250\mu\text{A}$	550			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	2.0		4.0	V
V_{SD}	Diode Forward On-Voltage	$I_S=4\text{A}; V_{GS}=0$			1.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=0.5\text{A}$			1.2	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}= \pm 30\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=550\text{V}; V_{GS}=0$			10	μA